

Band-structure trend in hole-doped cuprates and correlation with $T_{c\max}$.

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By calculation and analysis of the bare conduction bands in a large number of hole-doped high-temperature superconductors, we have identified the energy of the so-called axial-orbital as the essential, material-dependent parameter. It is uniquely related to the range of the intra-layer hopping. It controls the Cu 4s-character, influences the perpendicular hopping, and correlates with the observed T_c at optimal doping. We explain its dependence on chemical composition and structure, and present a generic tight-binding model.

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The mechanism of high-temperature superconductivity (HTSC) in the hole-doped cuprates remains a puzzle [1]. Many families with CuO_2 -layers have been synthesized and all exhibit a phase diagram with T_c going through a maximum as a function of doping. The prevailing explanation is that at low doping, superconductivity is destroyed with rising temperature by the loss of phase coherence, and at high doping by pair-breaking [2]. For the *materials*-dependence of T_c at optimal doping, $T_{c\max}$, the only known, but not understood, systematics is that for materials with multiple CuO_2 -layers, such as $\text{HgBa}_2\text{Ca}_{n-1}\text{Cu}_n\text{O}_{2n+2}$, $T_{c\max}$ increases with the number of layers, n , until $n \sim 3$. There is little clue as to why for n fixed, $T_{c\max}$ depends strongly on the family, *e.g.* why for $n=1$, $T_{c\max}$ is 40 K for La_2CuO_4 and 85 K for $\text{Tl}_2\text{Ba}_2\text{CuO}_6$, although the Neel temperatures are fairly similar. A wealth of structural data has been obtained, and correlations between structure and T_c have often been looked for as functions of doping, pressure, uniaxial strain, and family. However, the large number of structural and compositional parameters makes it difficult to find what besides doping controls the superconductivity. Insight was recently provided by Seo et al. [3] who grew ultrathin epitaxial $\text{La}_{1.9}\text{Sr}_{0.1}\text{CuO}_4$ films with varying degrees of strain and measured all relevant structural parameters and physical properties. For this single-layer material it was concluded that the distance between the charge reservoir and the CuO_2 -plane is the key structural parameter determining the normal state and superconducting properties.

Most theories of HTSC are based on a Hubbard model with *one* $\text{Cu } d_{x^2-y^2}$ -like orbital per CuO_2 unit. The one-electron part of this model is, in the $\mathbf{k}$ -representation:

$$\varepsilon(\mathbf{k}) = -2t(\cos k_x + \cos k_y) + 4t' \cos k_x \cos k_y - 2t''(\cos 2k_x + \cos 2k_y) + \dots, \quad (1)$$

with $t, t', t'', \dots$ denoting the hopping integrals (≥ 0) on the square lattice (Fig.1). First, only t was taken into account, but the consistent results of local-density approximation (LDA) band-structure calculations [4] and angle-resolved photoemission spectroscopy (for over-

doped, stripe-free materials) [5], have lead to the current usage of including also t' , with $t'/t \sim 0.1$ for La_2CuO_4 and $t'/t \sim 0.3$ for $\text{YBa}_2\text{Cu}_3\text{O}_7$ and $\text{Bi}_2\text{Sr}_2\text{CaCu}_2\text{O}_8$, whereby the constant-energy contours of expression (1) become rounded squares oriented in respectively the [11]- and [10]-directions. It is conceivable that the materials-dependence enters the Hamiltonian primarily via its one-electron part (1), and that this dependence is captured by LDA calculations. But it needs to be filtered out:

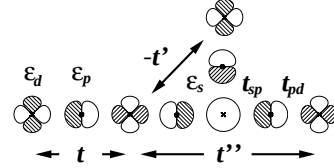


FIG. 1. Relation between the one-orbital model ($t, t', t'', \dots$) and the nearest-neighbor four-orbital model [4] ($\varepsilon_d - \varepsilon_p \sim 1 \text{ eV}$, $t_{pd} \sim 1.5 \text{ eV}$, $\varepsilon_s - \varepsilon_p \sim 16 - 4 \text{ eV}$, $t_{sp} \sim 2 \text{ eV}$).

The LDA band structure of the best known, and only stoichiometric optimally doped HTSC, $\text{YBa}_2\text{Cu}_3\text{O}_7$, is more complicated than what can be described with the t - t' model. Nevertheless, careful analysis has shown [4] that the *low-energy, layer-related* features, which are the only generic ones, can be described by a *nearest-neighbor, tight-binding* model with *four* orbitals per layer (Fig. 1), $\text{Cu } d_{x^2-y^2}$, $\text{O}_a p_x$, $\text{O}_b p_y$, and $\text{Cu } s$, with the interlayer hopping $t_{ss}^\perp$ proceeding via the diffuse $\text{Cu } s$ -orbital whose energy ε_s is several eV above the conduction band. Also the intralayer hoppings $t', t'', \dots$ beyond nearest neighbors in (1) proceed via $\text{Cu } s$. The constant-energy contours, $\varepsilon_i(\mathbf{k}) = \varepsilon$, of this model could be expressed simply as [4]:

$$1 - u - d(\varepsilon) + (1 + u)p(\varepsilon) = \frac{v^2}{1 - u + s(\varepsilon)} \quad (2)$$

in terms of the coordinates $u \equiv \frac{1}{2}(\cos k_x + \cos k_y)$ and $v \equiv \frac{1}{2}(\cos k_x - \cos k_y)$, and the quadratic functions

$$d(\varepsilon) \equiv \frac{(\varepsilon - \varepsilon_d)(\varepsilon - \varepsilon_p)}{4t_{pd}^2} \quad \text{and} \quad s(\varepsilon) \equiv \frac{(\varepsilon_s - \varepsilon)(\varepsilon - \varepsilon_p)}{4t_{sp}^2}$$

which describe the coupling of $O_{a/b} p_{x/y}$ to respectively $Cu d_{x^2-y^2}$ and $Cu s$. The term proportional to $p(\varepsilon)$ in (2) describes the admixture of $O_{a/b} p_z$ orbitals for dimpled layers and actually extends the four-orbital model to a six-orbital one [4]. For ε near the middle of the conduction band, $d(\varepsilon)$, $s(\varepsilon)$, and $p(\varepsilon)$ are positive, and the energy dependence of $d(\varepsilon)$ may be linearized ($d>0$), while that of $s(\varepsilon)$ and of $p(\varepsilon)$ may be neglected. $p=0$ for flat layers and $p=s^2/(1+s)^2$ for layers dimpled so as to yield extended saddlepoints. The bilayer bonding and antibonding subbands have ε_s -values split by $\mp t_{ss}^\perp$. Now, if ε_s were infinitely far above the conduction band, or t_{sp} vanishingly small, the right-hand side of (2) would vanish, with the result that the constant-energy contours would depend only on u . The dispersion of the conduction band near the Fermi level would thus be that of the one-orbital model (1) with $t=(1-p)/4d$ and $t'=t''=0$. For realistic values of ε_s and t_{sp} , the conduction band attains $Cu s$ -character proportional to v^2 , thus vanishing along the nodal direction, $k_x=k_y$, and peaking at $(\pi, 0)$, where it is of order 10 per cent. The repulsion from the $Cu s$ -band lowers the energy of the van Hove singularities and turns the constant-energy contours towards [10]. This same v^2 -dependence pertains to the interlayer splitting caused by $t_{ss}^\perp$ in a multilayer material. In order to go from (2) to (1),

$$\frac{1}{1-u+s} = \frac{2r}{1-2ru}, \quad \text{with } r \equiv \frac{1/2}{1+s}, \quad (3)$$

was expanded in powers of $2ru$. This provided explicit expressions, such as: $t = [1-p+o(r)]/4d$, $t' = [r+o(r)]/4d$, and $t'' = \frac{1}{2}t' + o(r)$, for the hopping integrals of the one-orbital model in terms of the parameters of the four(six)-orbital model and the expansion energy $\sim \varepsilon_F$. Note that all intralayer hoppings beyond nearest neighbors are expressed in terms of the *range*-parameter r . Although one may think of r as t'/t , this holds only for flat layers and when $r<0.2$. When $r>0.2$, the series (1) must be carried beyond t'' . Dimpling is seen not to influence the range of the intralayer hopping, but to reduce t through admixture of $O_{a/b} p_z$. In addition, it reduces t_{pd} .

Here, we shall generalize this analysis to all known families of HTSC materials using a new muffin-tin-orbital (MTO) method [6] which allows us to construct minimal basis sets for the low-energy part of an LDA band structure with sufficient accuracy that we can extract the materials dependence. This dependence, we find to be contained solely in ε_s , which is now the energy of the *axial* orbital, a hybrid between $Cu s$, $Cu d_{3z^2-1}$, apical-oxygen $O_c p_z$, and farther orbitals on *e.g.* La or Hg. The range, r , of the intralayer hopping is thus controlled by the structure and chemical composition *perpendicular* to the CuO_2 -layers. It turns out that the materials with the larger r (lower ε_s) tend to be those with the higher observed values of $T_{c \max}$. In the materials with the highest $T_{c \max}$, the axial orbital is almost pure $Cu 4s$.

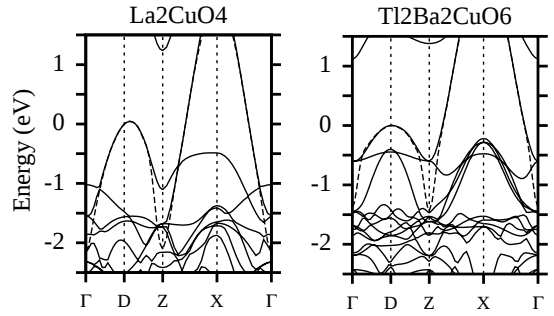


FIG. 2. LDA bands calculated with the NMTO method [6] in the body-centered tetragonal structure. The dashed band was obtained using the Bloch sum of MTOs with $N=0$ and $Cu d_{x^2-y^2}$ symmetry at the central site. Γ (0, 0, 0), D (π , 0, 0), Z (2π , 0, 0) = (0, 0, $2\pi/c$), X (π , π , 0).

It should be noted that r describes the *shape* of the non-interacting band in a 1eV-range around the Fermi level, whose accurate position is unknown because we make no assumptions about the remaining terms of the Hamiltonian, inhomogeneities, stripes, a.s.o.

Fig. 2 shows the LDA bands for the single-layer materials La_2CuO_4 and $Tl_2Ba_2CuO_6$. Whereas the high-energy band structures are complicated and very different, the low-energy conduction bands shown by dashed lines contain the generic features. Most notably, the dispersion along $\Gamma D Z$ is suppressed for $Tl_2Ba_2CuO_6$ relatively to La_2CuO_4 , whereas the dispersion along $\Gamma X Z$ is the same. This is the v^2 -effect. The low-energy bands were calculated variationally with a single Bloch sum of $Cu d_{x^2-y^2}$ -like orbitals, constructed to be correct at an energy near half-filling. Hence, these bands agree with the full band structures to linear order and head towards the pure $Cu d_{x^2-y^2}$ -levels at Γ and Z, extrapolating across a multitude of other bands. This was explained in Ref. [6]. Now, the hopping integrals t , t' , t'' , ... may be obtained by expanding the low-energy band as a Fourier series. This yields: $t=0.43$ eV in both cases, $t'/t=0.17$ for La_2CuO_4 and 0.33 for $Tl_2Ba_2CuO_6$, and many further inter- and intralayer hopping integrals [7].

That all these hopping integrals and their materials-dependence can be described with a generalized four-orbital model, is conceivable from the appearance of the conduction-band orbital for La_2CuO_4 in the xz -plane (Fig. 3). Starting from the central Cu atom and going in the x -direction, we see $3d_{x^2-y^2}$ antibond to neighboring $O_a 2p_x$, which itself bonds to $4s$ and antibonds to $3d_{3z^2-1}$ on the next Cu . From here, and in the z -direction, we see $4s$ and $3d_{3z^2-1}$ antibond to $O_c 2p_z$, which itself bonds to La orbitals, mostly $5d_{3z^2-1}$. In the y -direction, $4s$ antibonds and $3d_{3z^2-1}$ bonds to $O_b 2p_y$. For $Tl_2Ba_2CuO_6$, we find about the same amount of $Cu 3d_{x^2-y^2}$ and $O_{a/b} 2p_{x/y}$ character, but more $Cu 4s$, negligible $Cu 3d_{3z^2-1}$, much

less $O_c 2p_z$, and $Tl 6s$ instead of $La 5d_{3z^2-1}$ character. That is, in $Tl_2Ba_2CuO_6$ the axial part is mainly $Cu 4s$.

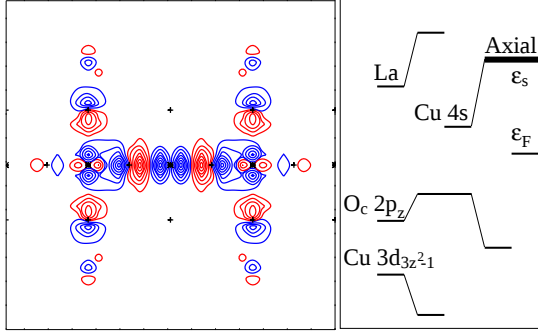


FIG. 3. *Left*: $N=0$ MTO describing the $Cu d_{x^2-y^2}$ -like conduction band in La_2CuO_4 . The plane is perpendicular to the layers and passes through Cu , O_a , O_c , and La . *Right*: Schematic diagram giving the energy ϵ_s of the *axial* orbital in terms of the energies of its constituents and their couplings.

Calculations with larger basis sets than one MTO per CuO_2 now confirm that, in order to localize the orbitals so much that only nearest-neighbor hoppings are essential, one needs to add *one* orbital, Cu axial, to the three standard ones [7]. The corresponding four-orbital Hamiltonian is therefore the one described above in Fig. 1 and Eqs. (2)-(3). Note, that we continue to call the energy of the axial orbital ϵ_s , and its hopping integral with $O_{a/b} p_{x/y}$ t_{sp} . Calculations with this basis set for many different materials show that, of all the parameters, only ϵ_s varies significantly [7]. This variation can be understood in terms of the couplings between the constituents of the axial orbital sketched in the right-hand panel of Fig. 3: We first form the appropriate $O_c p_z$ -like 5-atom hybrid $Cu d_{3z^2-1} - 2O_c p_z - 2La$ with the energy [7]

$$\epsilon_c = \epsilon_{\bar{c}} + \left(1 + \frac{t_{sc} t_{pz^2}}{t_{sp} t_{cz^2}}\right)^2 \frac{4\bar{r}t_{cz^2}^2}{\epsilon_F - \epsilon_{z^2}} - \frac{t_{cLa}^2}{\epsilon_{La} - \epsilon_F}, \quad (4)$$

and then couple this to the $Cu s$ -orbital to yield the energy $\epsilon_s = \epsilon_{\bar{s}} + 2t_{sc}^2/(\epsilon_F - \epsilon_c)$ of the axial orbital. Here, the energies of the pure $Cu s$ - and $O_c p_z$ -orbitals are denoted $\epsilon_{\bar{s}}$ and $\epsilon_{\bar{c}}$, respectively, while their hopping integral is t_{sc} . The energy of the $Cu d_{3z^2-1}$ -orbital is ϵ_{z^2} , and its hopping integrals to $O_{a/b} p_{x/y}$ and $O_c p_z$ are respectively t_{pz^2} and t_{cz^2} . In deriving Eqs. (2)-(4), we have exploited [7] that $t_{pz^2}^2/t_{sp}^2 \ll \frac{\epsilon_F - \epsilon_{z^2}}{\epsilon_{\bar{s}} - \epsilon_F}$ and that $t_{pd}^2/t_{sp}^2 \ll \frac{\epsilon_F - (\epsilon_p + \epsilon_d)/2}{\epsilon_F - (\epsilon_p + \epsilon_s)/2}$. Although specific for La_2CuO_4 , Eq. (4) is easy to generalize.

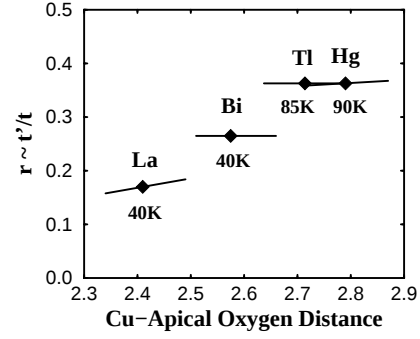


FIG. 4. Calculated range parameter, r , for single-layer materials vs. the distance (in Å) between Cu and O_c . The lines result from rigid displacements of O_c .

In Fig. 4 we plot the r -values for single-layer materials against the distance d_{Cu-O_c} between Cu and apical oxygen. r increases with d_{Cu-O_c} because ϵ_s is lowered towards ϵ_F when the coupling between $O_c p_z$ and $Cu d_{3z^2-1}/s$ is weakened. Since $t_{cz^2} \propto d_{Cu-O_c}^{-4}$ and $t_{sc} \propto d_{Cu-O_c}^{-2}$, increasing the distance suppresses the $Cu d_{3z^2-1}$ content, which is then important in La_2CuO_4 , but negligible in $Tl_2Ba_2CuO_6$ and $HgBa_2CuO_4$. This is also reflected in the slopes of the lines in Fig. 4 which give r vs. d_{Cu-O_c} for each material. The strong slope for La_2CuO_4 explains the findings of Seo *et al.* [3], provided that r correlates with superconductivity. That the Bi-point does not fall on the La-line is an effect of Bi being different from La: Bi $6p_z$ couples stronger to $O_c 2p_z$ than does $La 5d_{3z^2-1}$. The figure shows that upon reaching $HgBa_2CuO_4$, r is saturated, $\epsilon_s \sim \epsilon_{\bar{s}}$, and the axial orbital is almost purely $Cu 4s$.

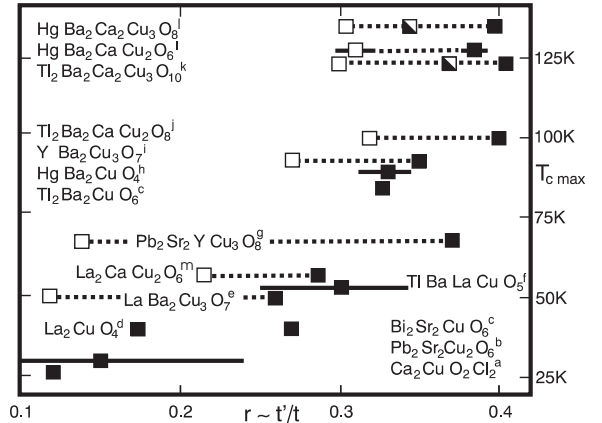


FIG. 5. Correlation between calculated r and observed $T_{c \max}$. *Filled squares*: Single-layer materials and most bonding subband for multilayers. *Empty squares*: Most antibonding subband. *Half-filled squares*: Non-bonding subband. *Dotted lines* connect subband-values. *Bars* give k_z -dispersion of r in primitive tetragonal materials. a-m [8–20]

Fig. 4 hints that for single-layer materials r might cor-

relate with the observed $T_{c\max}$. But the experimental uncertainties of both $T_{c\max}$ and the structural parameters are such that we need better statistics. Therefore, we plot the observed $T_{c\max}$ against the calculated r -values for nearly all known hole-doped HTSCs in Fig. 5. For the single-layer materials, we observe a strong correlation between r and $T_{c\max}$, which seems to be continued in the *bonding* subband for the multilayer materials (filled squares). This indicates that the electrons are delocalized over the multilayer [21], and that $T_{c\max}$ increases with the number of layers for the *same* reason that it increases among single-layer materials; the multilayer is simply a means of lowering ε_s further, through the formation of Cu 4s-Cu 4s bonding states. This is consistent with the celebrated pressure-enhancement [22] of T_c in HgBa₂Ca₂Cu₃O₈. One might attempt to increase $T_{c\max}$, say for YBa₂Cu₃O₇, by substituting Y with a smaller cation, *e.g.* Sc. This has not been done, but a *larger* cation, La, was recently inserted [12], and that caused $T_{c\max}$ to drop from 92 K to 50 K. Using the observed structure of LaBa₂Cu₃O₇, we have calculated the r -values and included them in Fig. 5. Here again, the bonding subband is seen to follow the trend! That $T_{c\max}$ eventually drops for an increasing number of layers, is presumably caused by loss of phase coherence.

Interlayer coupling in bct La₂CuO₄ mainly proceeds by hopping from $O_c p_z$ at $(0, 0, zc)$ to its four nearest neighbors at $(\pm\frac{1}{2}, \pm\frac{1}{2}, (\frac{1}{2} - z)c)$, and is therefore taken into account by adding to ε_c on the right-hand side of (4) the term $-8t_{cc}^\perp \cos\frac{1}{2}k_x \cos\frac{1}{2}k_y \cos\frac{1}{2}ck_z$. In primitive tetragonal materials, the corresponding term is merely $\propto \cos ck_z$ because the CuO₂-layers are stacked on top of each other, *e.g.* in HgBa₂CuO₄, the interlayer coupling proceeds from $O_c p_z$ at $(0, 0, zc)$ via Hg 6s/6p_z at $(0, 0, c/2)$ to $O_c p_z$ at $(0, 0, (1 - z)c)$. Periodic interlayer coupling thus makes ε_s depend on k_z , and this passes onto the conduction band a k_z -dispersion $\propto v^2 \cos\frac{1}{2}k_x \cos\frac{1}{2}k_y \cos\frac{1}{2}ck_z$ in bct and $\propto v^2 \cos ck_z$ in tetragonal structures. Fig. 5 shows how the k_z -dispersion of r decreases with contraction of the axial orbital.

Our identification of an electronic parameter, r or ε_s , which correlates with the observed $T_{c\max}$ for all known types of hole-doped HTSC materials should be a useful guide for materials synthesis and a key to understanding the mechanism of HTSC. With current $\mathbf{k}$ -space renormalization-group methods one could for instance investigate the effect of the band shape on the leading correlation-driven instabilities [23]. Moreover, the possibility that a longer hopping-range leads to better screening of the Coulomb repulsion, maybe even to overscreening, could be studied. Increased diagonal hopping, t' , might lead to higher $T_{c\max}$ by suppression of static stripe order [24]. The Van Hove scenario [25] finds no support in Fig. 5 because it is the saddlepoint of the *anti*-bonding band which is at the LDA Fermi level in YBa₂Cu₃O₇; the bonding band is about half-filled and enhances spin-

fluctuations with $\mathbf{q} \approx (\pi, \pi)$ [26]. The propensity to buckling is increased by pushing the conduction band towards the $O_{a/b} p_z$ -level by lowering of ε_s [4], but recent structural studies [12], as well as Fig. 5, disprove that static buckling enhances $T_{c\max}$, although dynamical buckling might. The interlayer-pair-tunnelling mechanism [27] is ruled out by the fact that the additional factor $\cos\frac{1}{2}k_x \cos\frac{1}{2}k_y$ attained by $t^\perp(\mathbf{k})$ in bct materials suppresses the interlayer pair-tunnelling in Tl₂Ba₂CuO₆ compared with HgBa₂CuO₄, and yet, $T_{c\max} \sim 90$ K in both cases. That the axial orbital is *the* channel for coupling the layer to its surroundings is supported [28] by the observations that the $\mathbf{k}$ -dependence of the scattering in the normal state is v^2 -like [5] and that the c -axis transport is strongly suppressed by the opening of a pseudogap [29] with similar $\mathbf{k}$ -dependence. The axial orbital is also *the* non-correlated vehicle for coupling between oxygens in the layer. Therefore it seems plausible that contraction of the axial orbital around the CuO₂-layer, away from the less perfect doping and insulating layers, will strengthen the phase coherence and thus increase $T_{c\max}$. Thermal excitation of nodal quasiparticles [30] is, on the other hand, hardly the mechanism by which the superconducting state is destroyed, because the axial orbital does not influence the band in the nodal direction. Finally, we note that the correlation between r and $T_{c\max}$ does not extend to electron-doped cuprates, where the mechanism for superconductivity thus seems to be different.

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